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Vishay Siliconix

## Automotive N-Channel 40 V (D-S) 175 °C MOSFET



PRODUCT SUMMARY				
V <sub>DS</sub> (V)	40			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0018			
I <sub>D</sub> (A)	330			
Configuration	Single			
Package	PowerPAK SO-8L			

#### **FEATURES**

- TrenchFET® Gen IV power MOSFET
- AEC-Q101 qualified
- 100 % R<sub>q</sub> and UIS tested
- Q<sub>gd</sub>/Q<sub>gs</sub> ratio < 1 optimizes switching characteristics
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912



GO	
N-Channel MOSFET	

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>C</sub> = 25 °C, unless otherwise noted)						
PARAMETER		SYMBOL	LIMIT	UNIT		
Drain-source voltage		V <sub>DS</sub>	40	V		
Gate-source voltage		$V_{GS}$	± 20	V		
Continuous drain current	T <sub>C</sub> = 25 °C	-	330			
	T <sub>C</sub> = 125 °C	I <sub>D</sub>	195			
Continuous source current (diode conduction)	I <sub>S</sub>	335	Α			
Pulsed drain current <sup>a</sup>	I <sub>DM</sub>	434				
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	39			
Single pulse avalanche energy	L = 0.1 IIIIA	E <sub>AS</sub>	76	mJ		
Maximum power dissipation <sup>a</sup>	T <sub>C</sub> = 25 °C	В	312	W		
	T <sub>C</sub> = 125 °C	$P_{D}$	104	VV		
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C		
Soldering recommendations (peak temperature) <sup>c</sup>			260			

THERMAL RESISTANCE RATINGS						
PARAMETER	SYMBOL	LIMIT	UNIT			
Junction-to-ambient	PCB mount b	$R_{thJA}$	42	°C/W		
Junction-to-case (drain)	on-to-case (drain)		0.48	G/VV		

#### Notes

- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- b. When mounted on 1" square PCB (FR4 material)
- c. See solder profile (<a href="www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection



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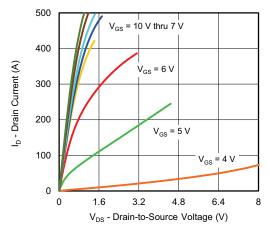
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static							•
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0$ , $I_D = 250 \mu A$		40	-	-	V
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	$V_{DS} = V_{GS}, I_{D} = 250 \mu\text{A}$		3.0	3.5	V
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA
		$V_{GS} = 0 V$	V <sub>DS</sub> = 40 V	-	-	1	
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 125 °C	-	-	50	μΑ
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = 40 V, T <sub>J</sub> = 175 °C	-	-	250	
On-state drain current <sup>a</sup>	I <sub>D(on)</sub>	V <sub>GS</sub> = 10 V	$V_{DS} \ge 5 \text{ V}$	30	-	-	Α
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A	-	0.0015	0.0018	
Drain-source on-state resistance a	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 125 °C	-	-	0.0024	Ω
		V <sub>GS</sub> = 10 V	I <sub>D</sub> = 15 A, T <sub>J</sub> = 175 °C	-	-	0.0028	
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub>	= 15 V, I <sub>D</sub> = 10 A	-	95	-	S
Dynamic <sup>b</sup>							
Input capacitance	C <sub>iss</sub>			-	3365	4715	pF
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	V <sub>DS</sub> = 25 V, f = 1 MHz	-	1110	1560	
Reverse transfer capacitance	C <sub>rss</sub>			-	53	80	
Total gate charge <sup>c</sup>	Qg			-	58	81	
Gate-source charge c	$Q_{gs}$	$V_{GS} = 10 \text{ V}$	$V_{DS} = 20 \text{ V}, I_D = 30 \text{ A}$	-	17	-	nC
Gate-drain charge c	$Q_{gd}$			-	9	-	
Gate resistance	Rg	f = 1 MHz		1	2.3	3.7	Ω
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	15.5	22	
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> =	$= 20 \text{ V}, R_L = 0.67 \Omega$	-	19	27	1
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 30 A$ ,	$I_D \cong 30 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		29	41	ns
Fall time <sup>c</sup>	t <sub>f</sub>				10	14	
Source-Drain Diode Ratings and Chara	acteristics <sup>b</sup>						
Pulsed current <sup>a</sup>	I <sub>SM</sub>				-	430	Α
Forward voltage	V <sub>SD</sub>	I <sub>F</sub> = 15 A, V <sub>GS</sub> = 0 V		-	-	1.1	V
Body diode reverse recovery time	t <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs		-	50	65	ns
Body diode reverse recovery charge	Q <sub>rr</sub>			-	48	61	nC
Reverse recovery fall time	ta			-	25	46	
Reverse recovery rise time	t <sub>b</sub>			-	25	46	ns
Body diode peak reverse recovery current	I <sub>RM(REC)</sub>			-	1.6	3	Α

#### Notes

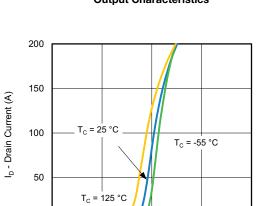
- a. Pulse test; pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





#### **Output Characteristics**



0

0

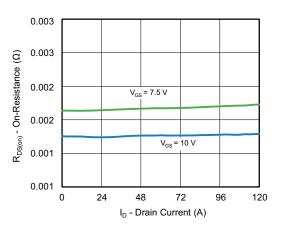
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V<sub>GS</sub> - Gate-to-Source Voltage (V) **Transfer Characteristics** 

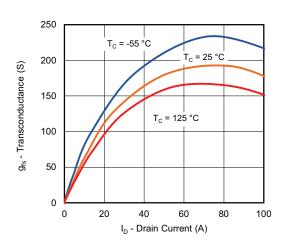
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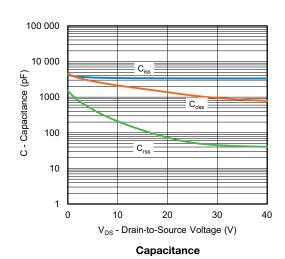
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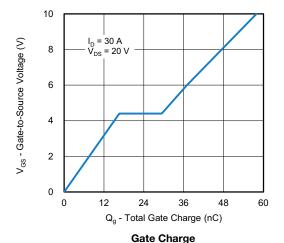
**On-Resistance vs. Drain Current** 

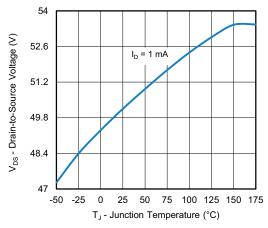


Transconductance

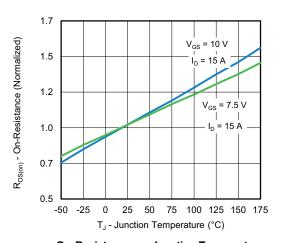


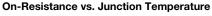


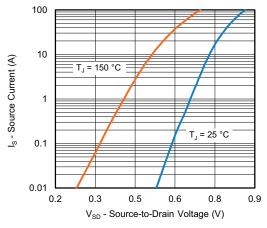




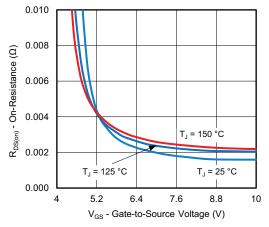
**Drain Source Breakdown vs. Junction Temperature** 





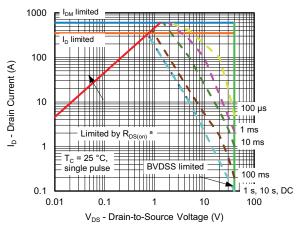


**Source Drain Diode Forward Voltage** 



On-Resistance vs. Gate-to Source Voltage

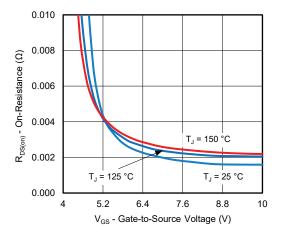




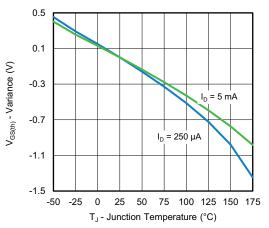
Safe Operating Area

#### Note

a.  $V_{GS} > minimum V_{GS}$  at which  $R_{DS(on)}$  is specified

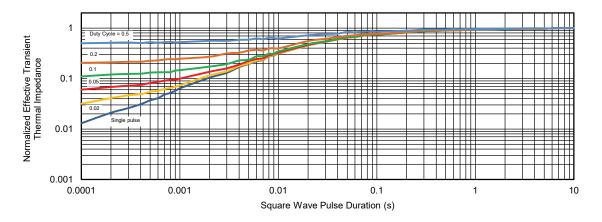


On-Resistance vs. Gate-to Source Voltage

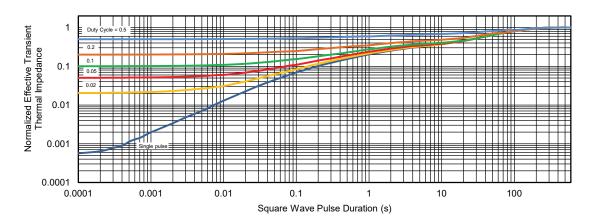


Threshold Voltage

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Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

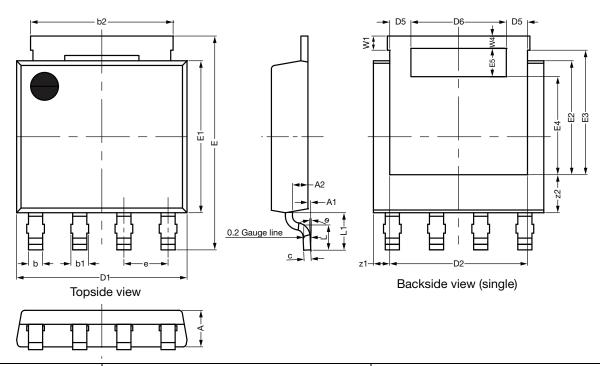
#### Note

- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77317.



## PowerPAK® SO-8L Case Outline 3



DIM.		MILLIMETERS		INCHES			
DIIVI.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.	
A	1.00	1.05	1.10	0.039	0.041	0.043	
A1	0.00		0.127	0.000		0.005	
A2	0.40	0.45	0.50	0.016	0.018	0.020	
b	0.33	0.41	0.49	0.013	0.016	0.019	
b1	0.43	0.51	0.59	0.017	0.020	0.023	
b2	4.00	4.10	4.20	0.157	0.161	0.165	
С	0.15	0.20	0.25	0.006	0.008	0.010	
D1	4.80	4.90	5.00	0.189	0.193	0.197	
D2	3.86	3.96	4.06	0.152	0.156	0.160	
D5	0.51	0.61	0.71	0.020	0.024	0.028	
D6	2.64	2.74	2.84	0.104	0.108	0.112	
е		1.27 BSC			0.050 BSC		
E	6.05	6.15	6.25	0.238	0.242	0.246	
E1	4.27	4.37	4.47	0.168	0.172	0.176	
E2	3.18	3.28	3.38	0.125	0.129	0.133	
E3	3.48	3.58	3.68	0.137	0.141	0.145	
E4	2.72	2.82	2.92	0.107	0.111	0.115	
E5	0.71	0.81	0.91	0.028	0.032	0.036	
L	0.62	0.72	0.82	0.024	0.028	0.032	
L1	0.92	1.07	1.22	0.036	0.042	0.048	
W1	0.31	0.41	0.51	0.012	0.016	0.020	
W4	0.31	0.36	0.41	0.012	0.014	0.016	
z1	0.37	0.47	0.57	0.015	0.019	0.022	
z2	0.99	1.09	1.19	0.039	0.043	0.047	
θ	0°		5°	0°		5°	

ECN: S19-0643-Rev. B, 05-Aug-2019

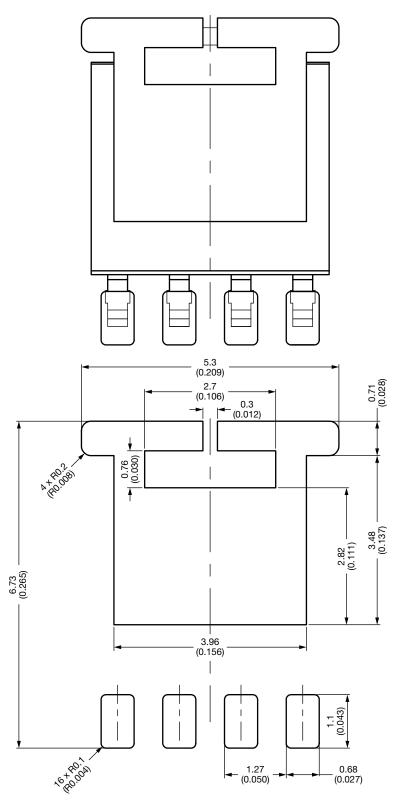
#### DWG: 6067 **Note**

• Millimeter will govern

Revison: 05-Aug-2019 1 Document Number: 76666



# Recommended Land Pattern PowerPAK® SO-8L Single Short Ear



Dimensions in Millimeters (Inches)



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